



cmos028fdsoi Technology

PDC vs MC Noise report for EG models

DK1.2\_RF\_mmW

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## General information on PDC vs MC Noise report for EG models

- Maximum supply voltage is 1.8 V.
- Validity domain is defined as follows:
  - ✓ Drawn gate length varies from 150nm to 10um.
  - ✓ Drawn transistor width varies from 0.16um to 10um.
  - ✓ Device temperature varies from -40 °C to 125 °C.

## Output parameters definitions

- Model(s): egnfet\_acc, egpfet\_acc

# egnfet\_acc

## Electrical characteristics per geometry

**egnfet\_acc @ w=1.5e-6, l=0.15e-6, pre\_layout\_local=1, nf=2, sa=1.2e-07, sb=1.2e-07, devtype=PCELLwoWPE, as=9e-14, ad=9e-14, ps=1.74e-06, pd=1.74e-06, vbs=0, vdd=1.8, temp=25**

	TT_Noisedev=4	TT_Noisedev=0	TT_Noisedev=2	PRO_MC_PARAM_ TT_1_MC_AVG-3S	PRO_MC_PARAM_ TT_1_MC_AVG	PRO_MC_PARAM_ TT_1_MC_AVG+3S
<b>logSi2@1Hz</b> [log10(A <sup>2</sup> /Hz)]	-16.72	-15.66	-14.59	-16.73	-15.66	-14.59
<b>logSi2ovId2@1Hz</b> [log10(1/Hz)]	-8.12	-7.06	-5.99	-8.12	-7.06	-5.99
<b>logSv2@1Hz</b> [log10(V <sup>2</sup> /Hz)]	-10.01	-8.94	-7.87	-10.01	-8.94	-7.87

# egpfet\_acc

## Electrical characteristics per geometry

**egpfet\_acc @ w=1.5e-6, l=0.15e-6, pre\_layout\_local=1, nf=2, sa=1.2e-07, sb=1.2e-07, devtype=PCELLwoWPE, as=9e-14, ad=9e-14, ps=1.74e-06, pd=1.74e-06, vbs=0, vdd=1.8, temp=25**

	TT_Noisedev=4	TT_Noisedev=0	TT_Noisedev=2	PRO_MC_PARAM_ TT_1_MC_AVG-3S	PRO_MC_PARAM_ TT_1_MC_AVG	PRO_MC_PARAM_ TT_1_MC_AVG+3S
<b>logSi2@1Hz</b> [log10(A <sup>2</sup> /Hz)]	-17.88	-16.98	-16.07	-17.88	-16.98	-16.07
<b>logSi2ovId2@1Hz</b> [log10(1/Hz)]	-8.48	-7.58	-6.68	-8.48	-7.58	-6.67
<b>logSv2@1Hz</b> [log10(V <sup>2</sup> /Hz)]	-10.1	-9.2	-8.3	-10.1	-9.2	-8.3



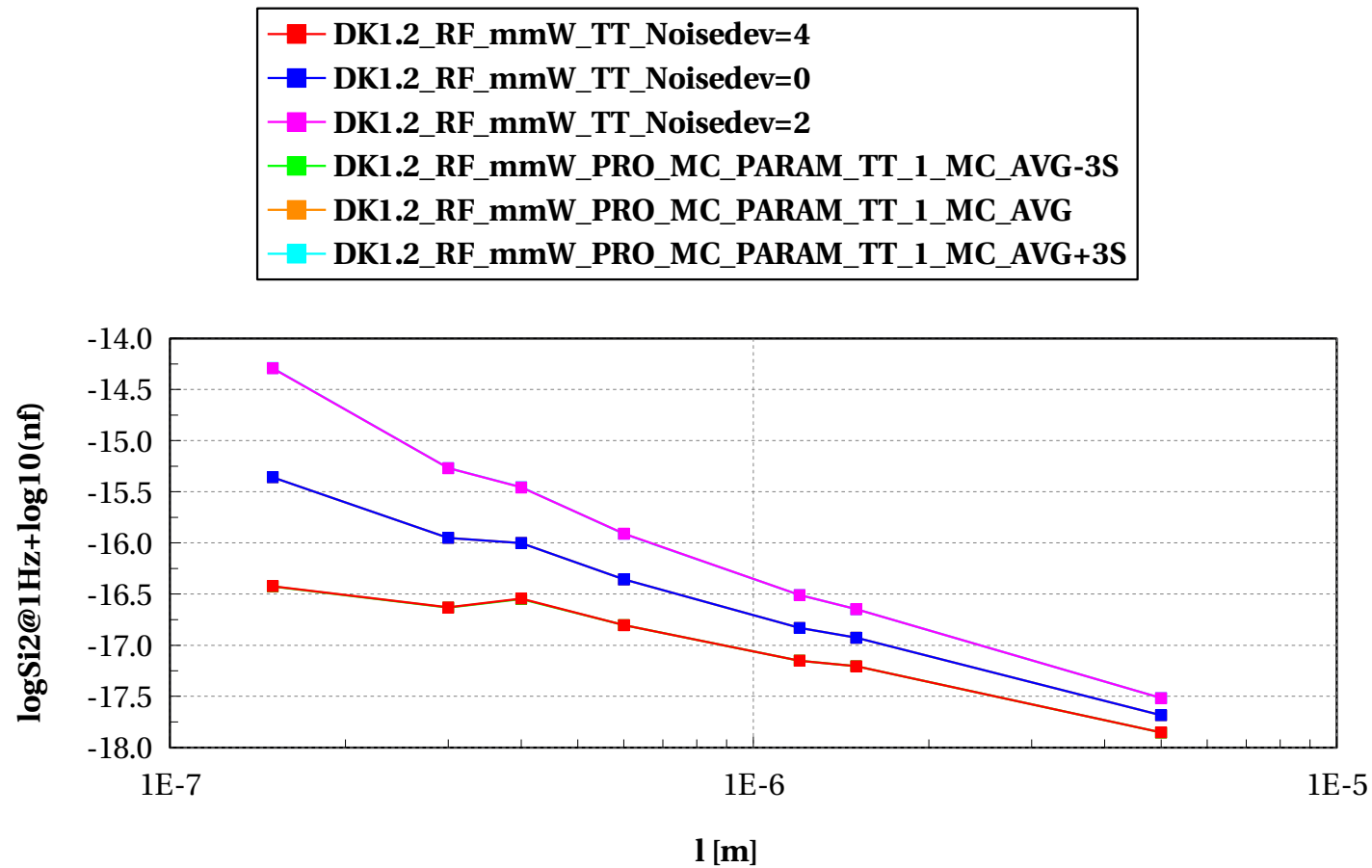
# egnfet\_acc

## Electrical characteristics scaling

## Scaling versus Length @ $W/L=10$ & $W/nf < 5\mu m$

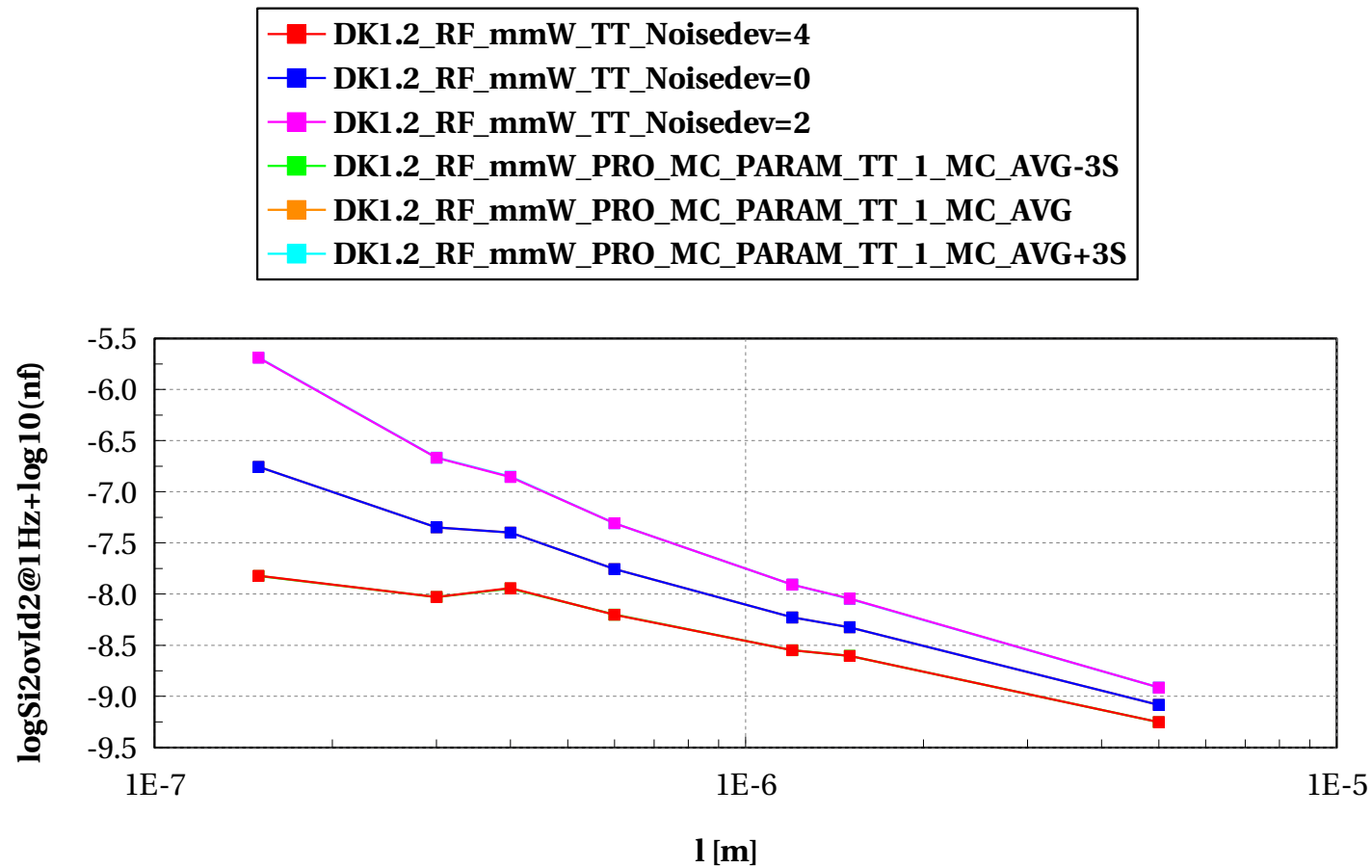
# egnfet\_acc, logSi2@1Hz+log10(nf) vs l [m]

W/L==10 and w/nf<5 and devType=="PCELLwoWPE"



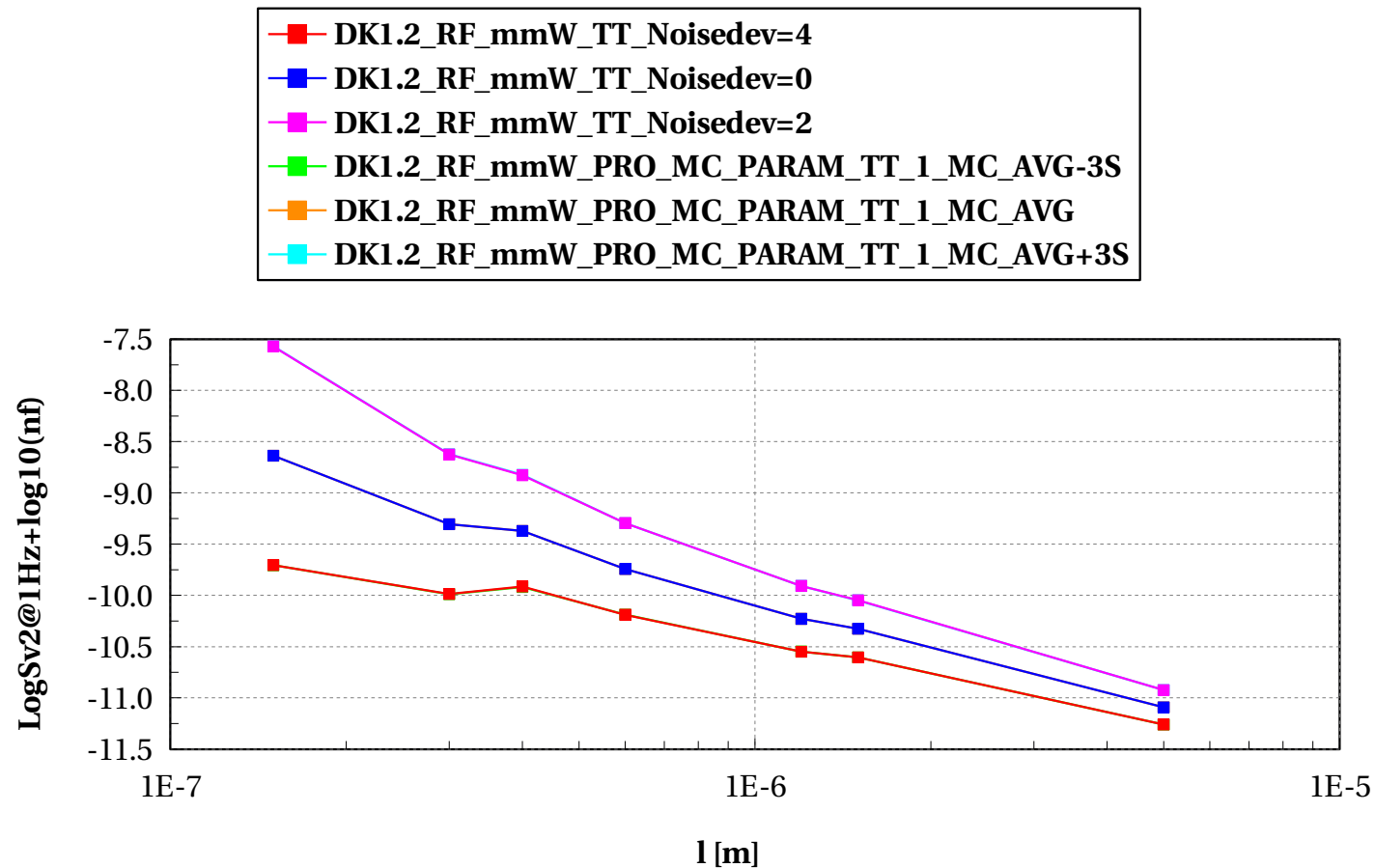
# egnfet\_acc, logSi2ovld2@1Hz+log10(nf) vs l [m]

W/L==10 and w/nf<5 and devType=="PCELLwoWPE"



# egnfet\_acc, LogSv2@1Hz+log10(nf) vs l [m]

W/L==10 and w/nf<5 and devType=="PCELLwoWPE"



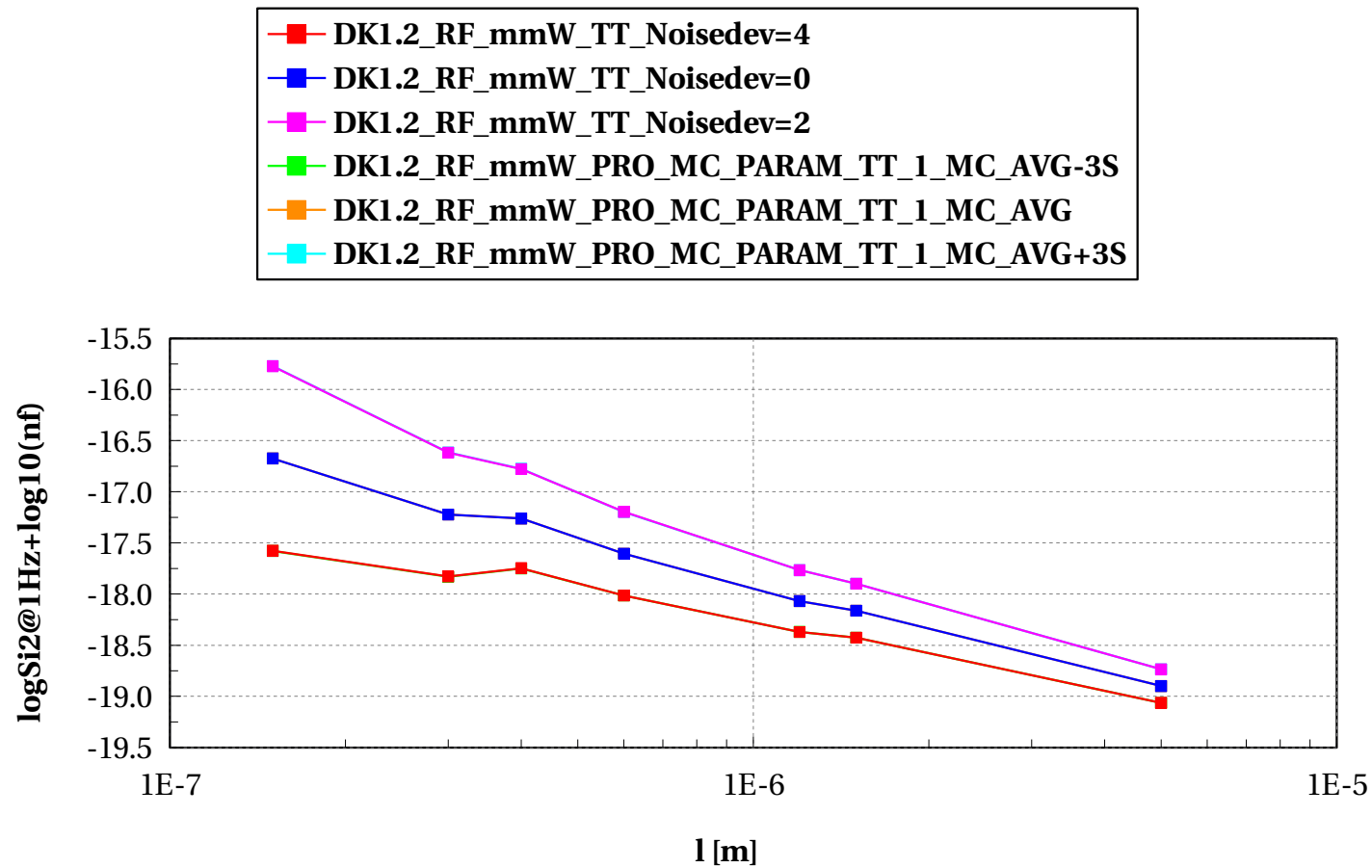
# egpfet\_acc

## Electrical characteristics scaling

## Scaling versus Length @ $W/L=10$ & $W/nf < 5\mu m$

# egpfet\_acc, logSi2@1Hz+log10(nf) vs l [m]

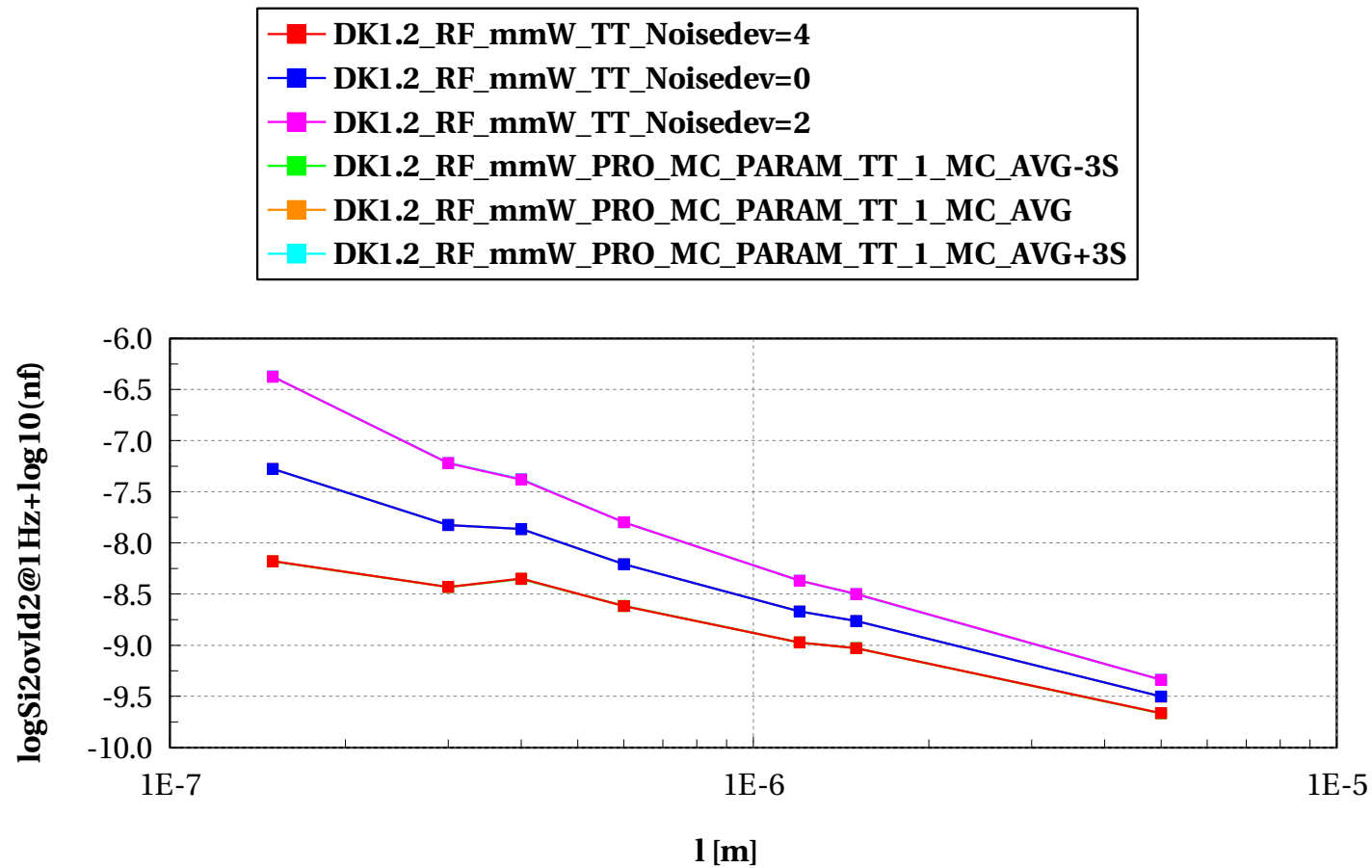
W/L==10 and w/nf<5 and devType=="PCELLwoWPE"





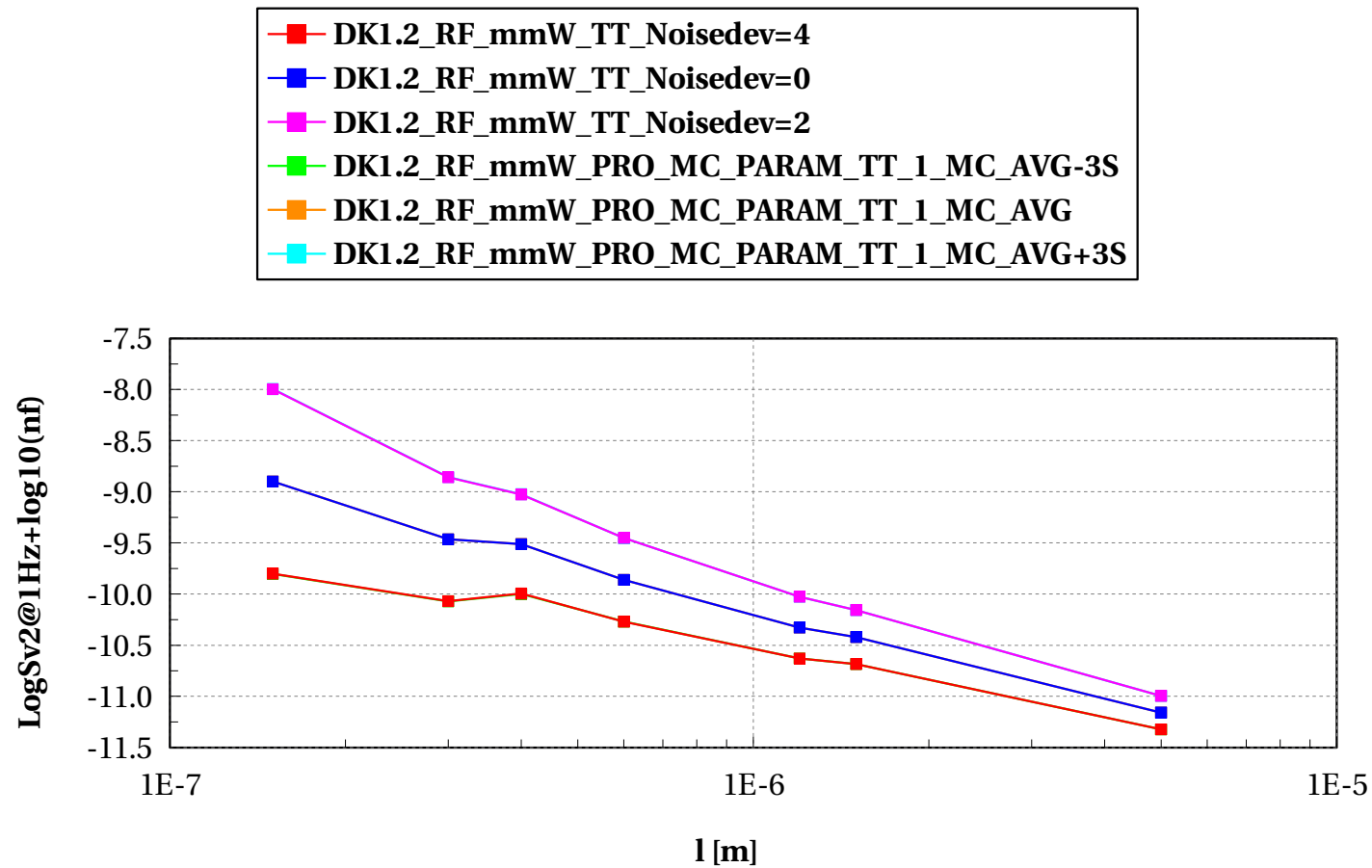
# egpfet\_acc, logSi2ovld2@1Hz+log10(nf) vs l [m]

W/L==10 and w/nf<5 and devType=="PCELLwoWPE"



# egpfet\_acc, LogSv2@1Hz+log10(nf) vs l [m]

W/L==10 and w/nf<5 and devType=="PCELLwoWPE"



# Annex

# Conditions of simulations

The simulations were done with SBenchLSF Alpha using Eldo simulator 2018.3.

- Model egfet\_acc (DK1.2\_RF\_mmW)

- ✓ Input Parameters

- ✗ ams\_release = 2018.3
- ✗ mc\_runs = 500
- ✗ iana = 5e-6 A
- ✗ temp = 25 °C
- ✗ mc\_sens = 0
- ✗ f\_ext = 100k Hz
- ✗ sbenchlsf\_release = Alpha
- ✗ vbs = 0 V
- ✗ model\_version = 1.2.c
- ✗ vds\_ana = Vdd/4 V
- ✗ mc\_nsigma = 3
- ✗ vdd = 1.8 V

- ✓ Sweep Parameters

- ✓ Extra parameters

- ✗ eg\_dev = 0
- Model egpfet\_acc (DK1.2\_RF\_mmW)
  - ✓ Input Parameters
    - ✗ ams\_release = 2018.3
    - ✗ mc\_runs = 500
    - ✗ iana = 2e-6 A
    - ✗ temp = 25 °C
    - ✗ mc\_sens = 0
    - ✗ f\_ext = 100k Hz
    - ✗ sbenchlsf\_release = Alpha
    - ✗ vbs = 0 V
    - ✗ model\_version = 1.2.c
    - ✗ vds\_ana = Vdd/4 V
    - ✗ mc\_nsigma = 3
    - ✗ vdd = 1.8 V
  - ✓ Sweep Parameters
  - ✓ Extra parameters
    - ✗ eg\_dev = 0